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			AUS9-2000-0734-US1		09/ 703,334	
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U.S. PATENT DOCUMENTS					
EXAMINER INITIAL	DOCUMENT NO.	PUBLICATION DATE	INVENTOR NAME	CLASS/ SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS					
EXAMINER INITIAL	DOCUMENT NO.	PUBLICATION DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES NO

OTHER PRIOR ART (including author, title, date, pertinent page, etc.)	
MLL	B. Prince, <u>Semiconductor Memories: A Handbook of Design, Manufacture, and Application, 2nd edition</u> , John Wiley & Sons, pp. 182-187, 07/1996.
MLL	Weinberg, "On tunneling in metal-oxide-silicon structures", <u>J. Appl. Phys.</u> , v. 53, n. 7, pp. 5052-5056, 07/1982.
MLL	Amin, "Design, selection, and implementation of flash erase EEPROM memory cells", <u>IEE Proceedings-G</u> , v. 139, n. 3, pp. 370-376, 06/1992.
MLL	Forbes, "Use of a spreadsheet for Fowler-Nordheim equation calculations", <u>J. Vac. Sci. Technol. B</u> , v. 17, n. 2, pp. 534-541, Mar/Apr. 1999.
MLL	Lenzlinger et al., "Fowler-Nordheim Tunneling into Thermally Grown SiO <sub>2</sub> ", <u>J. Appl. Phys.</u> , v. 40, n. 1, pp. 278-283, 01/1969.
MLL	Masuoka et al., "Reviews and Prospects of Non-Volatile Semiconductor Memories", <u>IEICE Transactions</u> , v. E 74, n. 4, 04/1991.
MLL	Masuoka et al., "Flash Memories, Their Status and Trends", <u>Proceedings of 4th Intl. Conf. on Solid-State and Integrated Circuit Technology</u> , pp. 128-132, 10/1995.
MLL	Chi et al., "True Low-Voltage Flash Memory Operations", <u>Proceedings of 1996 Intl. Nonvolatile Memory Technology Conference</u> , pp. 94-98, 04/1996.

DATE CONSIDERED	2/19/02	EXAMINER	Michael J. Ludwig
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